

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	325	438/476.ccls.	US-PGPUB; USPAT	OR	OFF	2006/10/06 10:32
L3	2303	438/151.ccls. 438/476.ccls. 438/791.ccls.	US-PGPUB; USPAT	OR	OFF	2006/10/06 11:03
L4	76	L3 and (getter\$6 same (sin "si. sub.3n.sub.4" "si.sub.3 n.sub.4" nitride))	US-PGPUB; USPAT	OR	ON	2006/10/06 11:03
L5	158	(getter\$6 with (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride)) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2006/10/06 11:11
L6	31	L5 same (tft gate source drain)	US-PGPUB; USPAT	OR	ON	2006/10/06 11:11
L7	135	getter\$6 and (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/06 11:19
L8	27	L7 and (tft gate source drain)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/06 11:19
L9	437	getter\$6 same (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2006/10/06 14:31
L10	8	getter\$6 same ((stress\$4 strain\$4 tensi\$6 compress\$6) with (dyne newton pascal pa mpa)) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2006/10/06 13:53
L11	38	getter\$6 same (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) same (sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4" nitride) same ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	US-PGPUB; USPAT	OR	ON	2006/10/06 12:15
L12	105	getter\$6 and (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/06 13:54

## EAST Search History

L13	22	getter\$6 same ((stress\$4 strain\$4 tensi\$6 compress\$6) with (dyne newton pascal pa mpa))	US-PGPUB; USPAT	OR	ON	2006/10/06 14:23
L14	29	(getter\$6 and (stress\$4 strain\$4 tensi\$6 compress\$6 dyne newton pascal pa mpa) and ((silicon si semiconductor epitax\$8 thin amorphous) near2 (film layer))). clm.	US-PGPUB	OR	ON	2006/10/06 14:32